MOSFET - N-Channel, SOT-23 500 mA, 60 V

Features

- NVBF Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage	V_{DGS}	60	Vdc
Gate-Source Voltage - Continuous - Non-repetitive (t _p ≤ 50 μs)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk
Drain Current - Continuous - Pulsed	I _D I _{DM}	0.5 0.8	Adc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1.) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.



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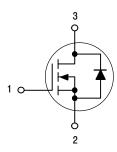
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500 mA, 60 V $R_{DS(on)} = 5 \Omega$

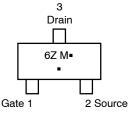


SOT-23 CASE 318 STYLE 21

N-Channel



MARKING DIAGRAM & PIN ASSIGNMENT



6Z = Specific Device Code

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

	Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	3	•	•		•
Drain-Source Breakdowr	n Voltage (V _{GS} = 0, I _D = 100 μA)	V _{(BR)DSS}	60	_	Vdc
Gate-Body Leakage Cur	I _{GSS}	-	10	nAdc	
ON CHARACTERISTICS	(Note 1)				
Gate Threshold Voltage (V _{GS(th)}	0.8	3.0	Vdc	
Static Drain-Source On-	r _{DS(on)}	-	5.0	Ω	
On-State Drain Current (I _{D(off)}	_	0.5	μΑ	
DYNAMIC CHARACTERI	STICS				
Input Capacitance (V _{DS} = 10 Vdc, V _{GS} = 0	0 V, f = 1.0 MHz)	C _{iss}	-	60	pF
SWITCHING CHARACTE	RISTICS (Note 1)		•		•
Turn-On Delay Time	$(V_{DD}$ = 25 Vdc, I_{D} = 500 mA, R_{gen} = 50 Ω)	t _{d(on)}	-	10	ns
Turn-Off Delay Time	Figure 1	t _{d(off)}	-	10	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping [†]		
MMBF170LT1G	SOT-23 (TO-236) (Pb-Free)	3000 / Tape & Reel		
MMBF170LT3G	SOT-23 (TO-236) (Pb-Free)	10000 / Tape & Reel		
NVBF170LT1G*	SOT-23 (TO-236) (Pb-Free)	3000 / Tape & Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

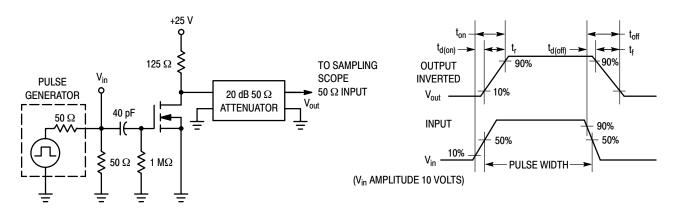


Figure 1. Switching Test Circuit

Figure 2. Switching Waveform

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

TYPICAL ELECTRICAL CHARACTERISTICS

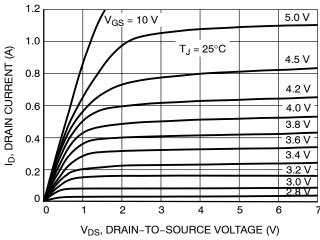


Figure 3. On-Region Characteristics

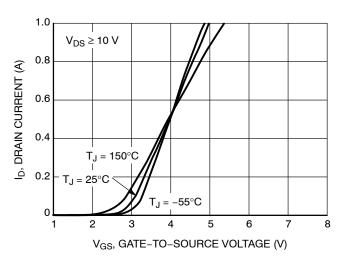


Figure 4. Transfer Characteristics

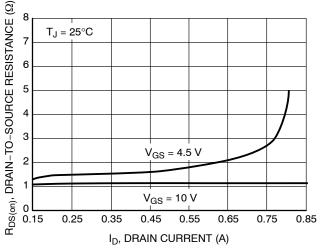


Figure 5. On-Resistance vs. Drain Current and Gate Voltage

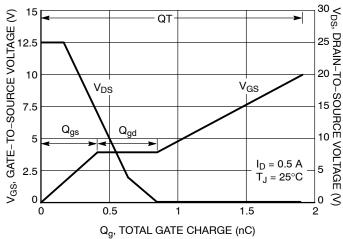


Figure 6. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

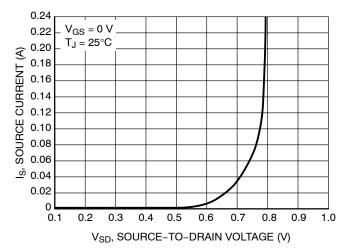


Figure 7. Diode Forward Voltage vs. Current

TYPICAL ELECTRICAL CHARACTERISTICS

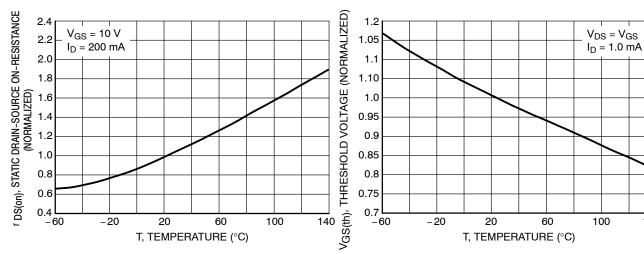


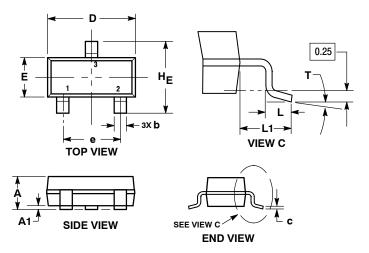
Figure 8. Temperature versus Static Drain-Source On-Resistance

Figure 9. Temperature versus Gate Threshold Voltage

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PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**



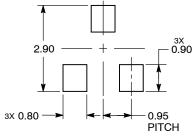
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 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10 °	0 °		10 °

STYLE 21:

- PIN 1. GATE
 - 2. SOURCE
 - DRAIN

RECOMMENDED **SOLDERING FOOTPRINT***



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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